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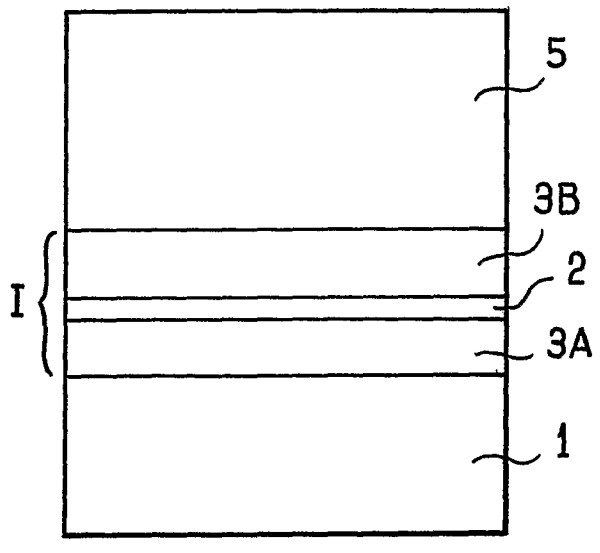
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(54) Title: RECYCLING OF A WAFER COMPRISING A MULTI-LAYER STRUCTURE AFTER TAKING-OFF A THIN LAYER



(57) Abstract: Method of recycling a donor wafer (10) after having taken off a useful layer comprising a material chosen from semiconductor materials, the donor wafer (10) comprising successively a substrate (1) and a multi-layer structure (I), the multi-layer structure (I), before taking-off, comprising the useful layer to take off, the process comprising removal of substance on the side where the taking-off took place, characterized in that, after the removal of substance, at least a part of the multi-layer structure (I') remains, this at least part of the buffer structure (I') including at least one other useful layer that can be taken off, without a supplementary step of reforming a useful layer. This document also relates to: methods of taking-off a thin layer from at least one recyclable donor wafer (10) according to the invention, recyclable donor wafers (10) according to the invention.

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